PNP/NPN Epitaxial Planar Silicon Transistors

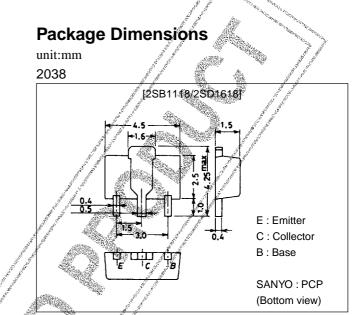


2SB1118/2SD1618

Low-Voltage High-Current Amplifier, **Muting Applications**

Features

- · Low collector-to-emitter saturation voltage.
- · Very small size making it easy to provide highdensity, small-sized hybrid IC's.



(): 2SB1118

140 s 280

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter		Symbol / Conditions	Ratings	Unit
Collector-to-Base Voltage		VCBO	(–)20	V
Collector-to-Emitter Voltage		VCEO	(–)15	V
Emitter-to-Base Voltage		VEBO	(–)5	V
Collector Current	A		(-)0.7	A
Collector Current (Pulse)	A STATE	ICP /	(–)1.5	A
Collector Dissipation	and a start	Be.	500	mW
	and the second	Mounted on ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	all a start and a start a		150	°C
Storage Temperature	é	Tstg	-55 to +150	°C

Electrical Characteristics at Ta = 25 °C

1 N N N N N N N N N N N N N N N N N N N	Symbol	Conditions	Ratings			Unit
Falailleta	yinooi		min	typ	max	Onit
Collector Cutoff Current	сво /	V _{CB} =(–)15V, I _E =0			(–)0.1	μA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(–)0.1	μA
DC Current Gain	bF∉1	V _{CE} =(-)2V, I _C =(-)50mA	140*		560*	
Cain Randwidth Broduct	hFE2	V _{CE} =(-)2V, I _C =(-)500mA	60			
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)50mA		250		MHz

 \ast ; The 2SB(1)8/2SD1618 are classified by 50mA h_{FE} as follows : 200 T 400

280 U 560

Marking 2SB1118 : BA 2SD1618 : DA

hFE rank : S, T, U

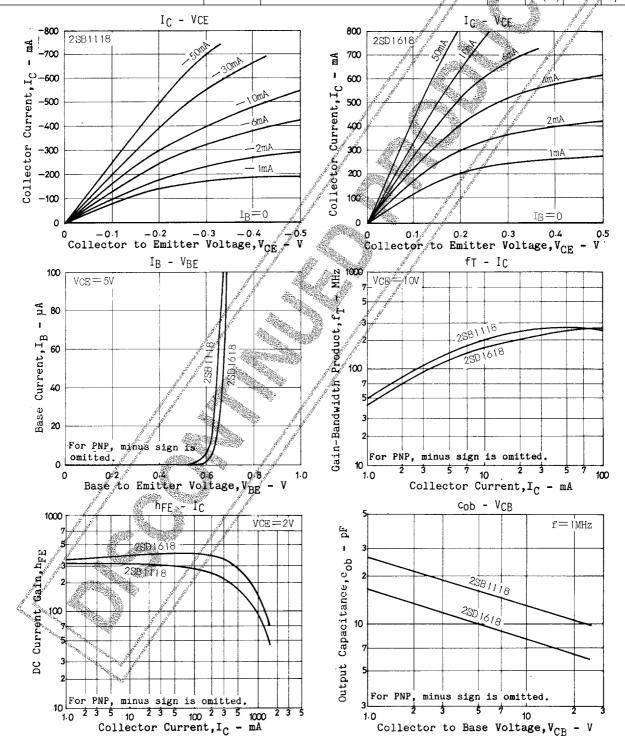
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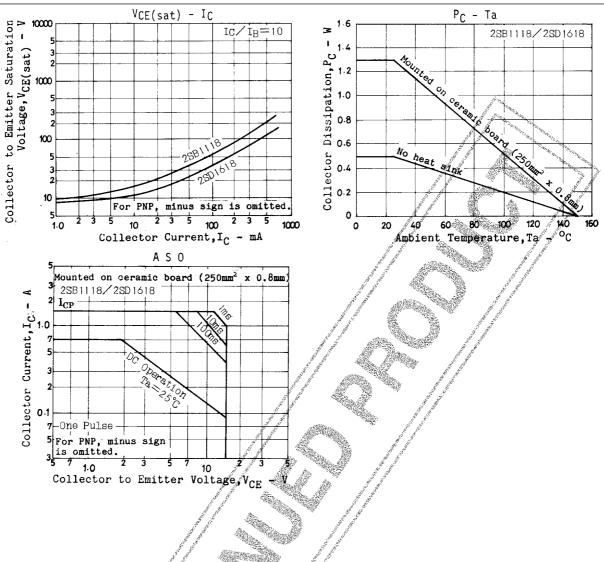
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2SB1118/2SD1618

Deremeter	Cumhal	Conditions		Ratings			Linit
Parameter	Symbol		Γ	min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)} 1	I _C =(-)5mA, I _B =(-)0.5mA			10	25	mV
			Г		(–15)	(–35)	mV
	V _{CE(sat)} 2	I _C =(–)100mA, I _B =(–)10mA		.:	30	80	mV
			Γ	all the second	(–60)	(–120)	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)100mA, I _B =(-)10mA		A all and a second	(–)0.8	(–)1.2	V
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)10μA, I _E =0	1	<u>(</u> –)20	and the second	Sterlin Str.	V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	and the second second	[*] (–)15,		South Harrison	V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(–)10μA, I _C =0	ALC AND	(–)5		Sec. Sec. Sec.	N.V
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz	* ²⁵	1997 1997	8	li li	фF
		[S. SANO	(13)	and the second second	pF



2SB1118/2SD1618



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